NSN 5962-01-445-4426

Memory Microcircuit - Page 1 of 2

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Body Length:

1.680 inches

Body Width:

Between 0.510 inches and 0.620 inches

Body Height:

0.225 inches

Maximum Power Dissipation Rating:

1.0 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

F-15i

Features Provided:

Burn in, mil-std-883, class b and electrostatic sensitive and hermetically sealed and monolithic and tested to mil-std-883 and electrically alterable

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Complementary-metal oxide-semiconductor logic

Input Circuit Pattern:

17 input

Criticality Code Justification:

Cbbl

Case Outline Source And Designator:

D-16 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Microcircuit, memory, digital, cmos, 128k x 8 bit 5-volt programming eeprom, monolithic silicon

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 6.0 volts power source

Capitance Rating Per Characteristic:

6.00 input picofarads and 12.00 output picofarads

Time Rating Per Chacteristic:

120.00 nanoseconds access

Memory Device Type:

Eeprom

Special Features:

Case outline source and designator is mil-std-1835, gdip1-t32 or cdip2-t32; endurance is 1000 cycles

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufacturer standards, etc.).

Terminal Type And Quantity:

32 printed circuit

Specification Data:

67268-5962-91682 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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